

Mark T Winkler

List of Publications by Year in descending order

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Version: 2024-02-01

20
papers

4,441
citations

430442

18
h-index

794141

19
g-index

20
all docs

20
docs citations

20
times ranked

4737
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|------|-----------|
| 1 | Device Characteristics of CZTSSe Thin-Film Solar Cells with 12.6% Efficiency. <i>Advanced Energy Materials</i> , 2014, 4, 1301465. | 10.2 | 2,651 |
| 2 | Room-temperature sub-band gap optoelectronic response of hyperdoped silicon. <i>Nature Communications</i> , 2014, 5, 3011. | 5.8 | 202 |
| 3 | Optical designs that improve the efficiency of $\text{Cu}_2\text{ZnSn}(\text{S},\text{Se})_4$ solar cells. <i>Energy and Environmental Science</i> , 2014, 7, 1029-1036. | 15.6 | 200 |
| 4 | Light-induced water oxidation at silicon electrodes functionalized with a cobalt oxygen-evolving catalyst. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2011, 108, 10056-10061. | 3.3 | 195 |
| 5 | Insulator-to-Metal Transition in Sulfur-Doped Silicon. <i>Physical Review Letters</i> , 2011, 106, 178701. | 2.9 | 167 |
| 6 | Pulsed-laser hyperdoping and surface texturing for photovoltaics. <i>MRS Bulletin</i> , 2011, 36, 439-445. | 1.7 | 150 |
| 7 | Insulator-to-Metal Transition in Selenium-Hyperdoped Silicon: Observation and Origin. <i>Physical Review Letters</i> , 2012, 108, 026401. | 2.9 | 141 |
| 8 | Hall mobility of cuprous oxide thin films deposited by reactive direct-current magnetron sputtering. <i>Applied Physics Letters</i> , 2011, 98, . | 1.5 | 120 |
| 9 | Nitrogen-doped cuprous oxide as a p-type hole-transporting layer in thin-film solar cells. <i>Journal of Materials Chemistry A</i> , 2013, 1, 15416. | 5.2 | 108 |
| 10 | The role of diffusion in broadband infrared absorption in chalcogen-doped silicon. <i>Applied Physics A: Materials Science and Processing</i> , 2009, 96, 327-334. | 1.1 | 85 |
| 11 | Pressure-induced phase transformations during femtosecond-laser doping of silicon. <i>Journal of Applied Physics</i> , 2011, 110, . | 1.1 | 79 |
| 12 | Atomic Layer Deposited Aluminum Oxide for Interface Passivation of $\text{Cu}_2\text{ZnSn}(\text{S},\text{Se})_4$ Thin-Film Solar Cells. <i>Advanced Energy Materials</i> , 2016, 6, 1600198. | 10.2 | 75 |
| 13 | Supersaturating silicon with transition metals by ion implantation and pulsed laser melting. <i>Journal of Applied Physics</i> , 2013, 114, . | 1.1 | 59 |
| 14 | Interfaces between water splitting catalysts and buried silicon junctions. <i>Energy and Environmental Science</i> , 2013, 6, 532-538. | 15.6 | 58 |
| 15 | Picosecond carrier recombination dynamics in chalcogen-hyperdoped silicon. <i>Applied Physics Letters</i> , 2014, 105, . | 1.5 | 42 |
| 16 | Mid-infrared absorptance of silicon hyperdoped with chalcogen via fs-laser irradiation. <i>Journal of Applied Physics</i> , 2013, 113, . | 1.1 | 37 |
| 17 | Studying femtosecond-laser hyperdoping by controlling surface morphology. <i>Journal of Applied Physics</i> , 2012, 111, 093511. | 1.1 | 35 |
| 18 | Extended X-ray absorption fine structure spectroscopy of selenium-hyperdoped silicon. <i>Journal of Applied Physics</i> , 2013, 114, 133507. | 1.1 | 25 |

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|----|--|-----|-----------|
| 19 | Selenium Segregation in Femtosecond-Laser Hyperdoped Silicon Revealed by Electron Tomography. Microscopy and Microanalysis, 2013, 19, 716-725. | 0.2 | 10 |
| 20 | Growth and p-type doping of cuprous oxide thin-films for photovoltaic applications. , 2012, , . | | 2 |